

### **isc Silicon NPN Power Transistor**

## 2SC3678

#### DESCRIPTION

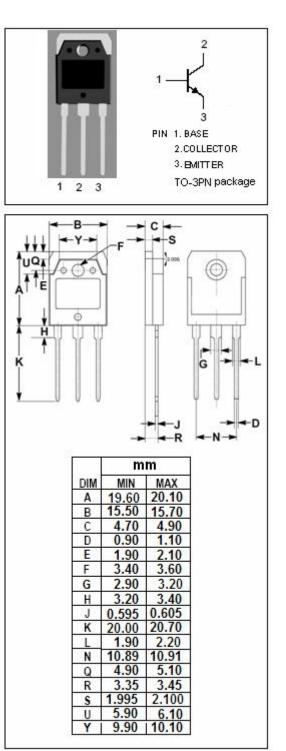
- · High Collector-Emitter Breakdown Voltage-: V<sub>(BR)CEO</sub>= 800V(Min)
- · High Switching Speed
- High Reliability
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

• Designed for switching regulator and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)						
SYMBOL	PARAMETER	VALUE	UNIT			
Vсво	Collector-Base Voltage	900	V			
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V			
V <sub>EBO</sub>	Emitter-Base voltage	7	V			
lc	Collector Current-Continuous	3	A			
I <sub>CM</sub>	Collector Current-Peak	6	A			
I <sub>B</sub>	Base Current-Continuous	1.5	A			
Pc	Collector Power Dissipation @ $T_c$ =25 °C	80	W			
TJ	Junction Temperature	150	°C			
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C			

### ABSOLUTE MAXIMUM PATINGS/T-=25 m





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### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{c}}\text{=}25^{\circ}\!\!\!^{\circ}\!\!^{\circ}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT	
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA ; I <sub>B</sub> = 0	800			V	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.2A			0.5	V	
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.2A			1.2	V	
І <sub>сво</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> = 0			0.1	mA	
Іево	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			0.1	mA	
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V	10		30		
f⊤	Current-Gain—Bandwidth Product	I <sub>E</sub> = -0.3A; V <sub>CE</sub> = 12V		6		MHz	
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1.0MHz		50		pF	
Switching times							

t <sub>on</sub>	Turn-on Time			1.0	μ <b>s</b>
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 1A, I <sub>B1</sub> = 0.15A; I <sub>B2</sub> = -0.5A R <sub>L</sub> = 250 Ω ; V <sub>CC</sub> = 250V		5.0	μs
t <sub>f</sub>	Fall Time			1.0	μ S

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